



- Low forward voltage and leakage current
- Low inductance package
- High surge current capability

V_{RRM}	2000	V
$I_D(@ T_C = 100^\circ\text{C})$	75	A
$I_{FSM}(@ t_p = 10\text{ms})$	750	A
$V_{FM}(\text{Max})$		

- Field supply for DC motors
- Line rectifiers for transistorized AC motor controllers
- Non-controllable rectifiers for AC/DC converter

(@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RRM}	2000	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RSM}	2100	V
Average forward current	$T_C = 100^\circ\text{C}$	I_D	75	A
Forward surge current	1/2 cycle, Sine wave, 50Hz $T_{vj} = 25$	I_{FSM}	750	A
I^2t value for fusing		I^2t	2810	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_{vj}	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	



(@ $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Peak forward voltage	$I_F=75\text{A}$, $t_P=380\mu\text{s}$	V_{FM}		1.20	1.40	V
Reverse leakage current	$V_R = V_{RRM}$, $T_{vj} = 25$	I_{RRM}			0.2	mA
	$V_R = V_{RRM}$, $T_{vj} = 150$				3	mA
Threshold voltage	$T_{vj} = 150$, for power loss calculation only	V_{TO}			0.92	V
Dynamic resistance		r_T			4.8	m Ω

(@ $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Thermal resistance, junction to case	per diode	$R_{th(j-c)}$			1.3	K/W
Thermal resistance, case to heatsink	per module	$R_{th(c-s)}$			0.2	K/W
Mounting torque	Module and heatsink fixed torque	M	2.5		3.5	N m

JMD75TD20D0	JMD75TD20D0	D0	78g/PCS	28PCS	140PCS

FIG.1: Forward characteristics(per diode)

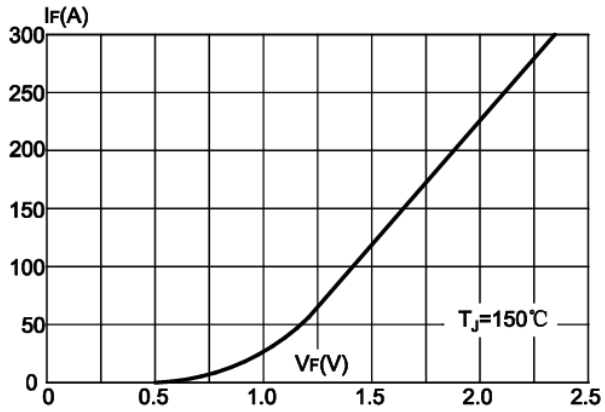


FIG.2: Peak on-state surge current

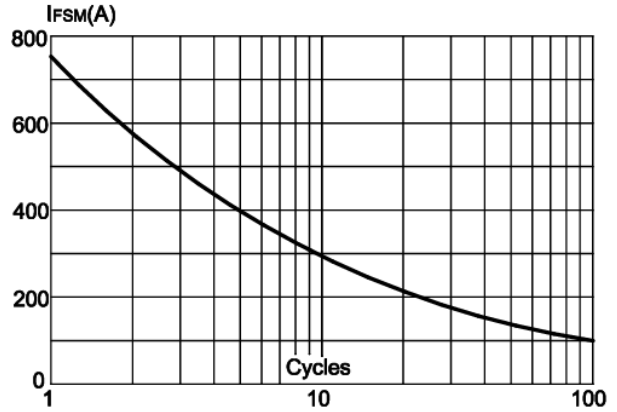
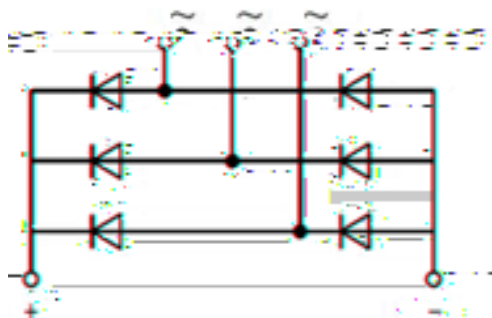
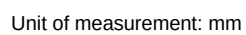


FIG.3: Forward current vs. case temperature



FIG.4: Maximum transient thermal impedance







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